

HVR100

Variable Capacitance Diode for AM tuner

HITACHI

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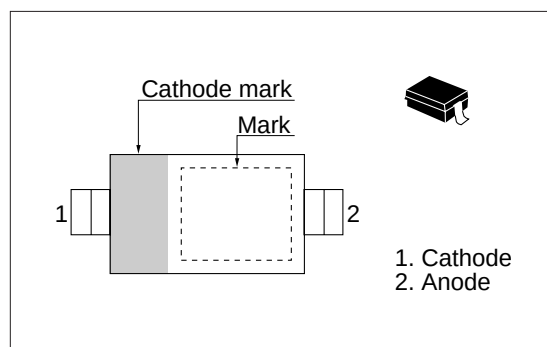
Features

- High capacitance ratio. ($n = 16.0$ min)
- High figure of merit. ($Q = 200$ min)
- To be usable at low voltage.
- Small Resin Package (SRP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HVR100	2	SRP

Outline



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Value	Unit
Reverse voltage	V_R	15	V
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	15	—	—	V	$I_R = 10 \mu\text{A}$
Reverse current	I_R	—	—	100	nA	$V_R = 9 \text{ V}$
Capacitance	C_1	421.5	—	524.6	pF	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$
	C_3	182.0	—	275.7		$V_R = 3 \text{ V}, f = 1 \text{ MHz}$
	C_5	73.2	—	121.4		$V_R = 5 \text{ V}, f = 1 \text{ MHz}$
	C_6	42.2	—	72.2		$V_R = 6 \text{ V}, f = 1 \text{ MHz}$
	C_7	26.2	—	41.6		$V_R = 7 \text{ V}, f = 1 \text{ MHz}$
	C_8	20.4	—	28.2		$V_R = 8 \text{ V}, f = 1 \text{ MHz}$
Capacitance ratio	n	16.0	—	—	—	C_1 / C_8
Figure of merit	Q	200	—	—	—	$C = 450 \text{ pF}, f = 1 \text{ MHz}$
Matching error	$\Delta C/C^*$	—	—	3.0	%	$V_R = 1 \sim 8 \text{ V}$
ESD-Capability	—	80	—	—	V	* $C = 200 \text{ pF}$, Both forward and reverse direction 1 pulse.

* Failure Criterion ; $I_R \geq 100 \text{ nA}$ at $V_R = 9 \text{ V}$

** A set of HVR100 is of uniform C-V characteristics.

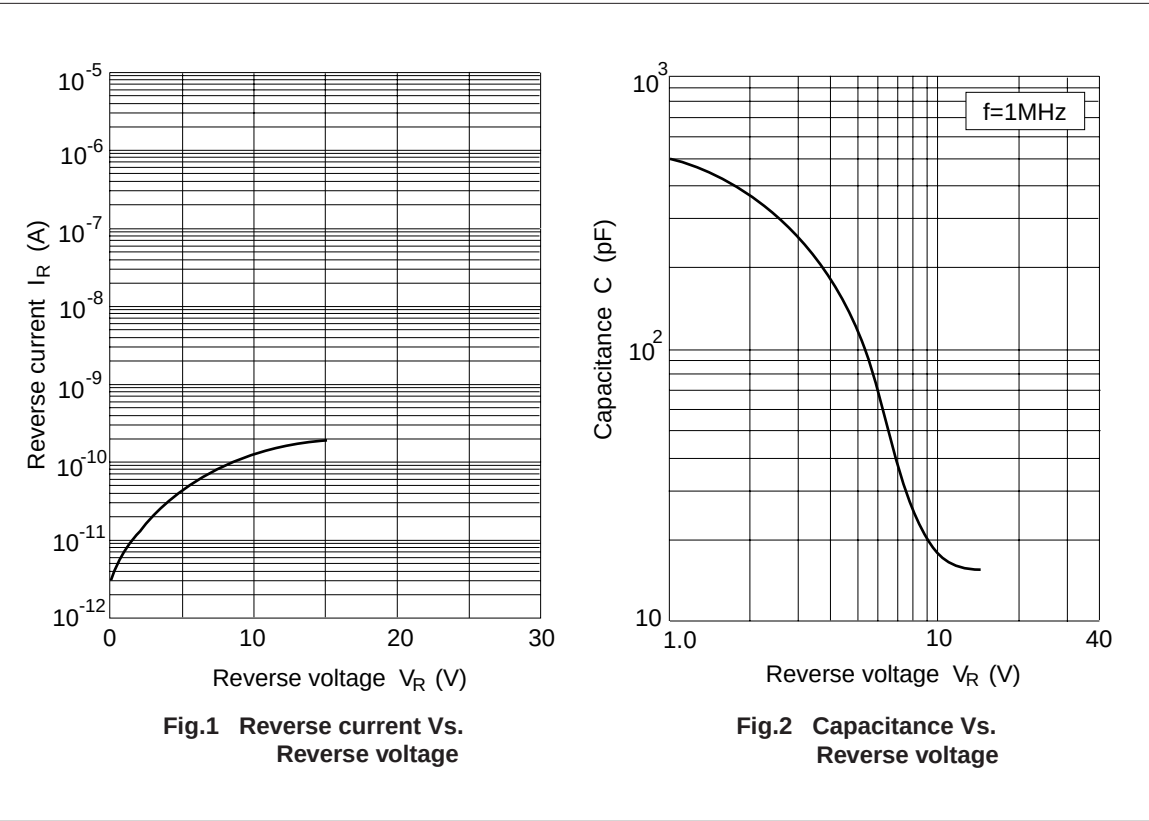
Measure max. value and min. value of capacitance at each bias point of $V_R = 1 \text{ V}$ through 8 V .

Calculate Matching Error,

$$\Delta C/C = \frac{(C_{\text{max}} - C_{\text{min}})}{C_{\text{min}}} \times 100 (\%)$$

***Each group shall uniform a multiple of 3 diodes.

HVR100



Package Dimensions

Unit: mm

